

sPHENIX EMCal

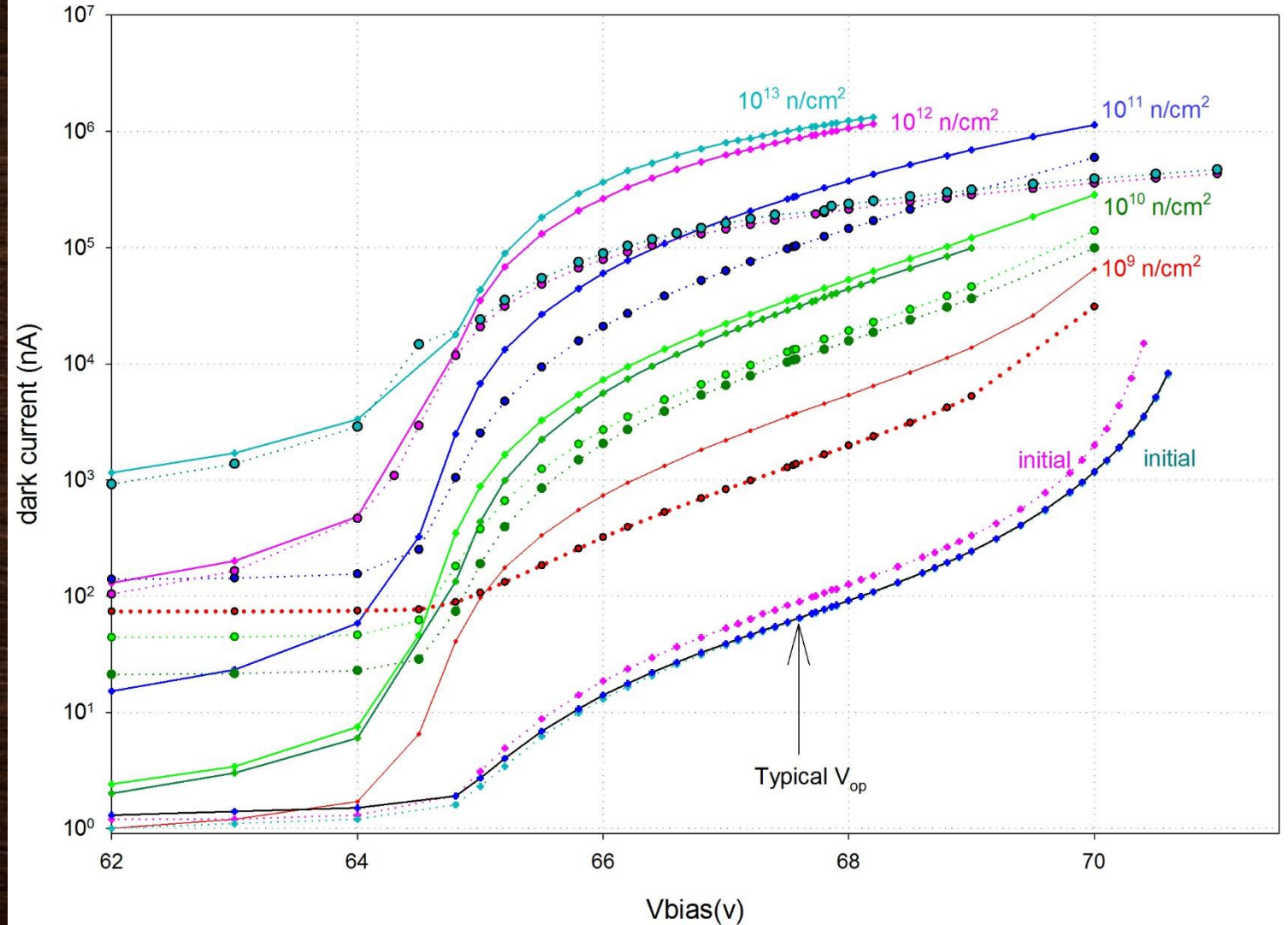
Electronics/SiPM R&D at BNL

SEAN STOLL

UIUC SPHENIX EMCAL WORKFEST 8/2015

radiation damage:
increased dark (supply) current
with exposure

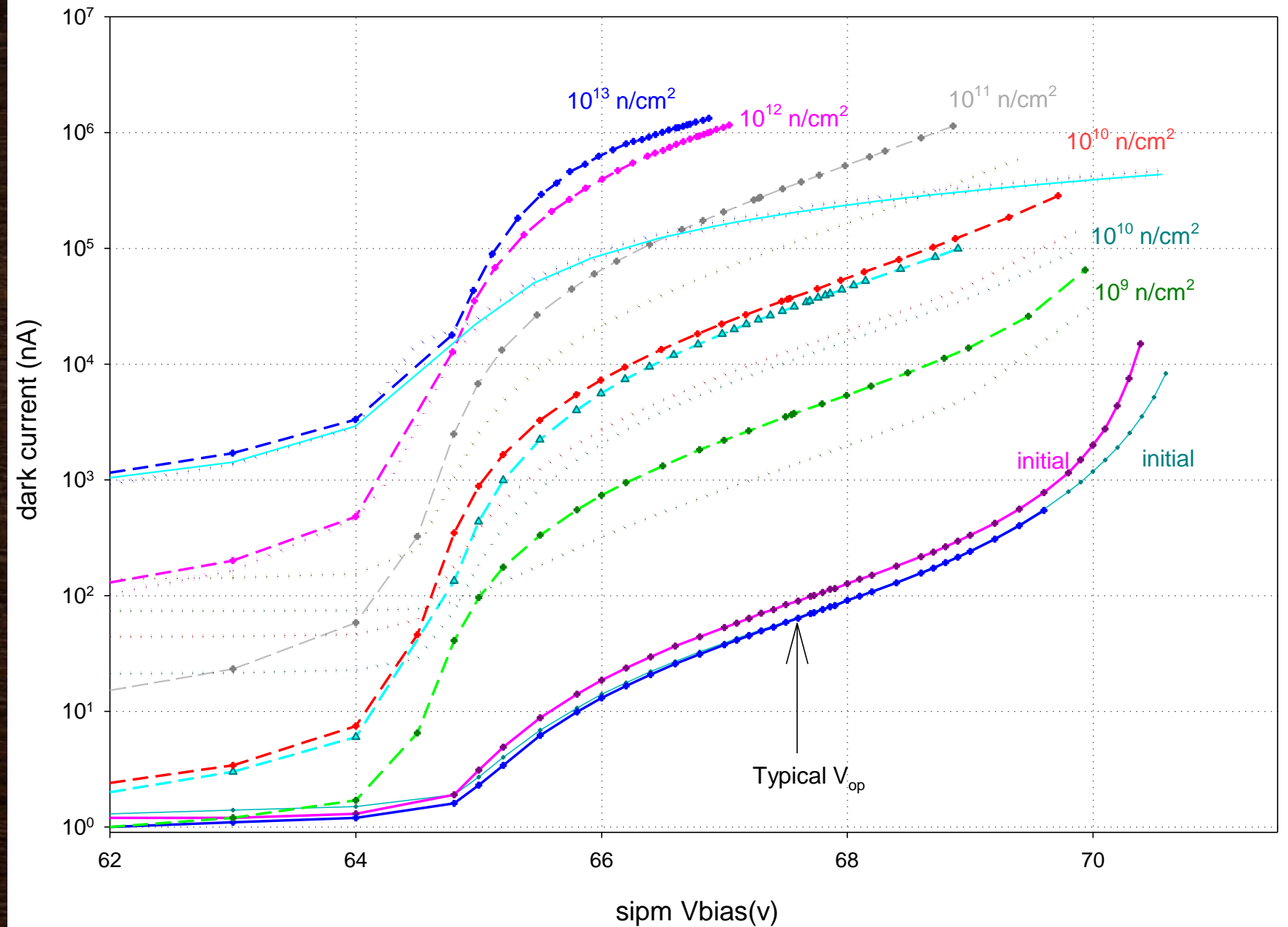
Note (added 8/17): As discussed at the mtg, V_{bias} here is the total supply voltage. It would be better to plot this vs ΔV across the sipm, which would result in slightly higher post-irradiation currents. Correceted graph is in the next slide.



radiation damage:
increased dark current
with exposure.

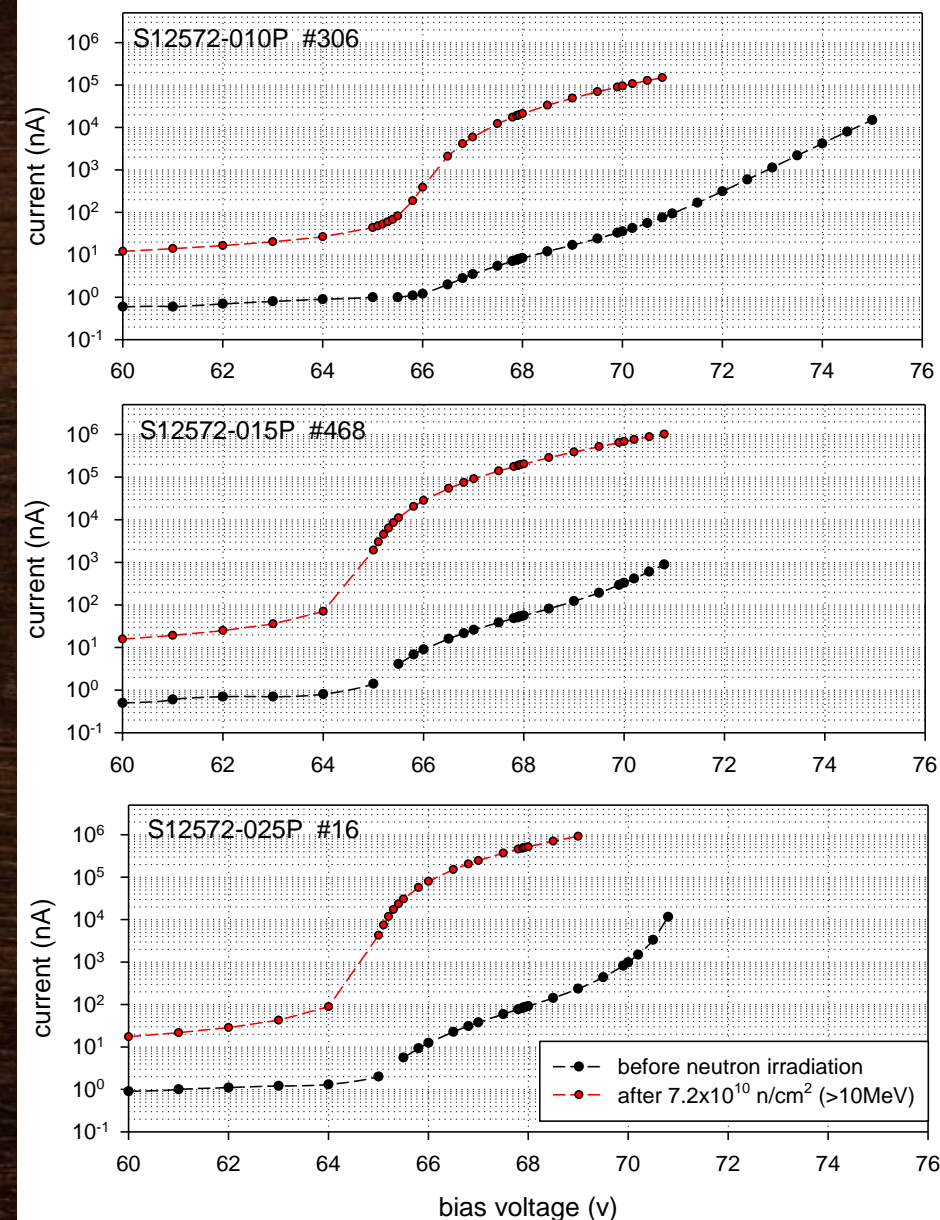
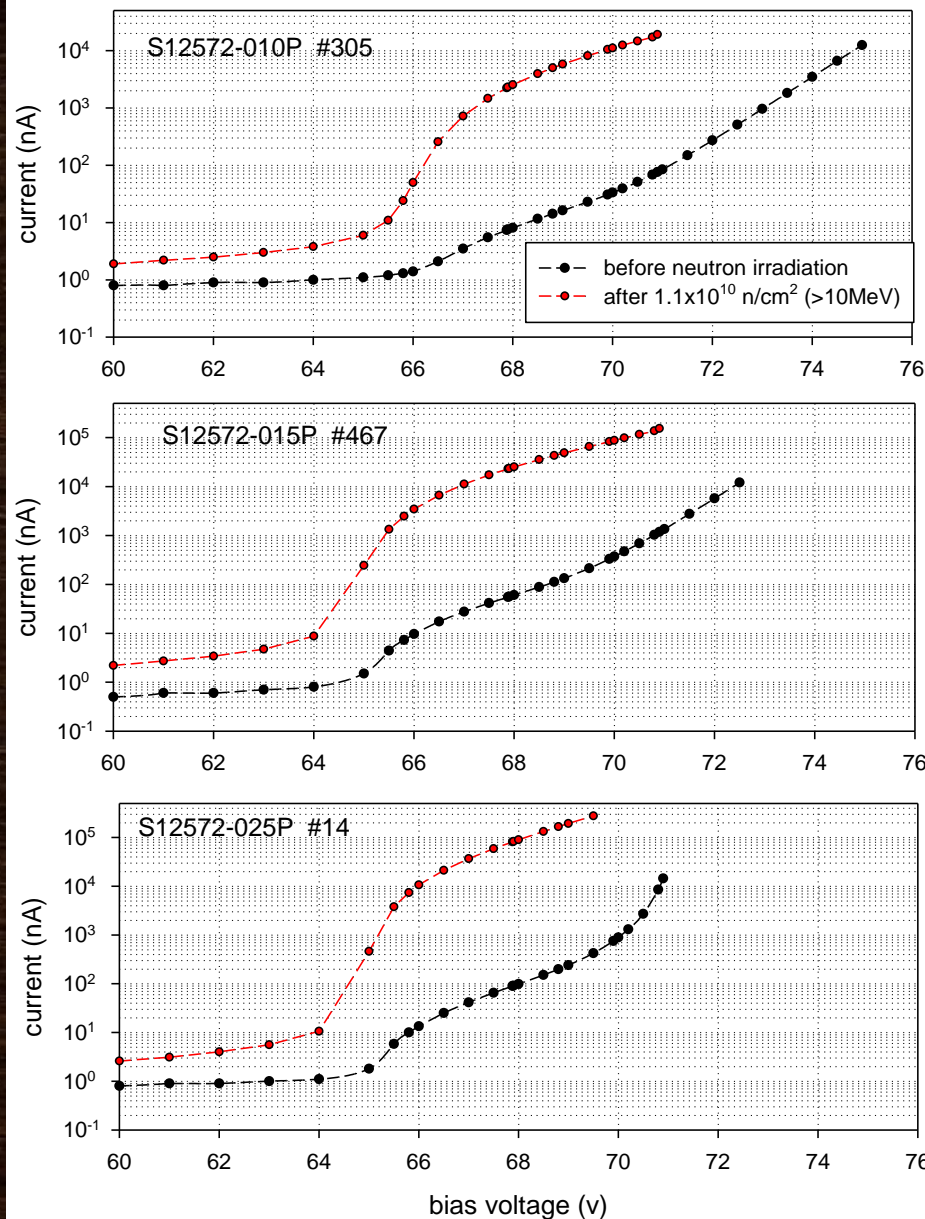
Dark current as a function of
bias voltage across sipm –
corrected for voltage drops
across other resistive circuit
elements.

The dotted curves show
recovery (decrease) in current
with time, after irradiation.



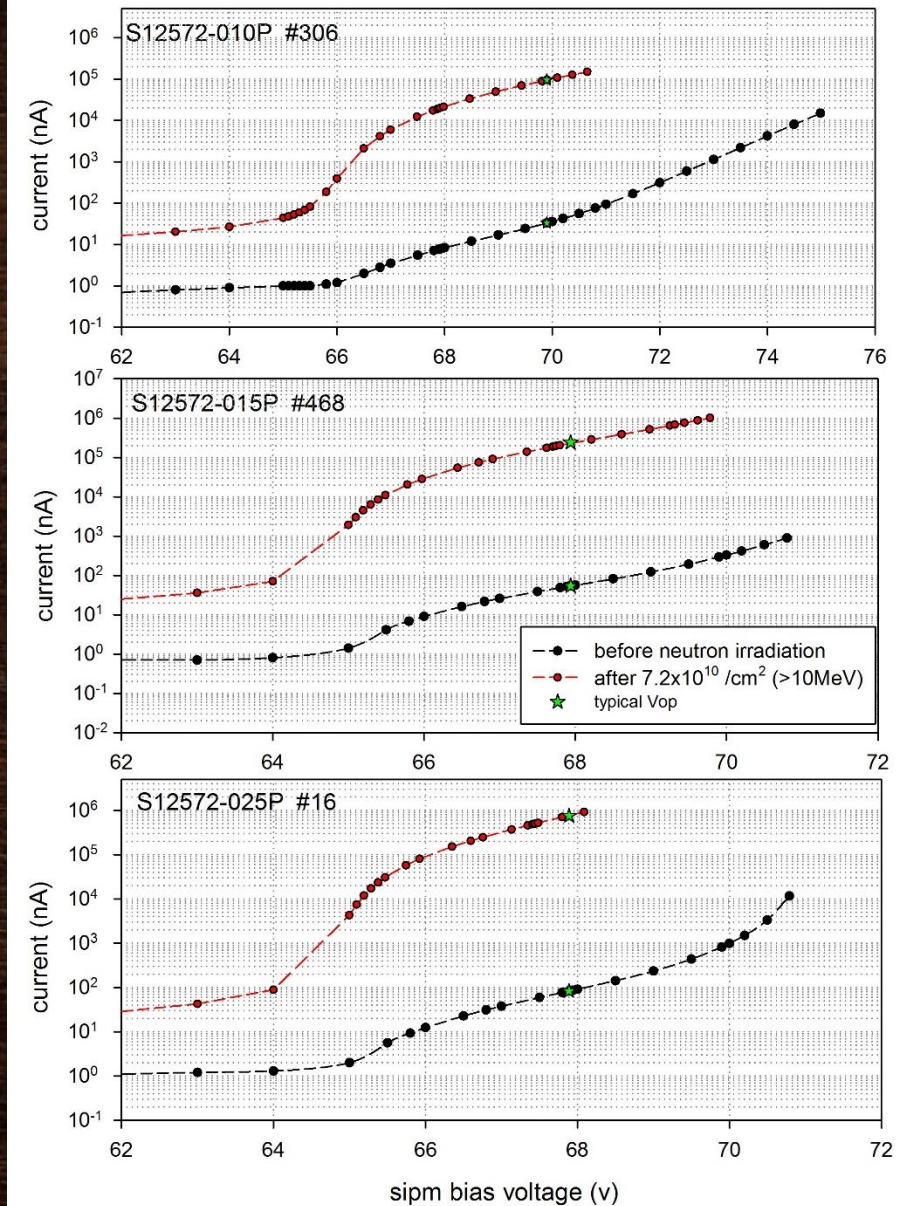
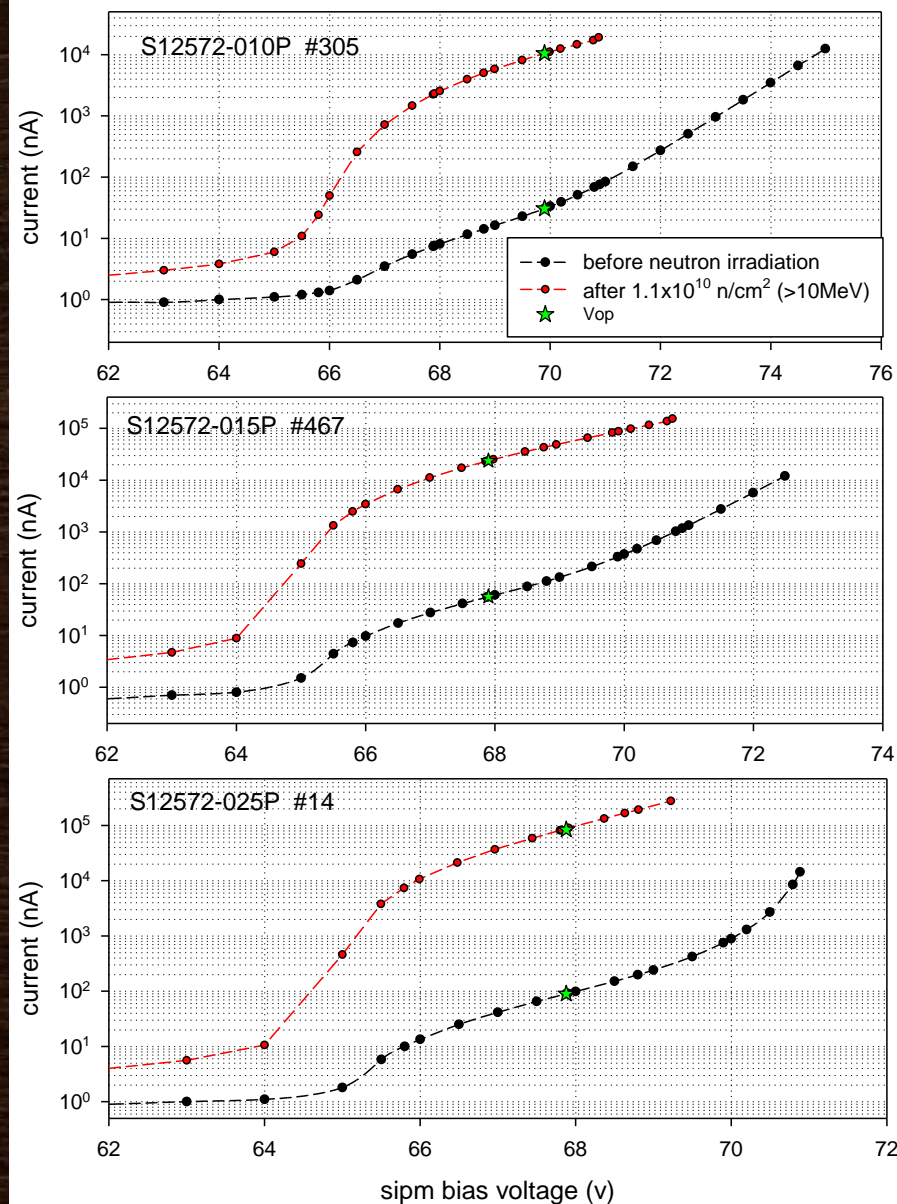
neutron irradiation at LANSCE

*Note (added 8/17):
As discussed at the
mtg, V_{bias} here is
the total supply
voltage. It would be
better to plot this
vs ΔV across
the sipm, which
would result in
slightly higher
post-irradiation
currents. See next
slide for corrected
plots.*



Dark current vs bias voltage, measured before and after irradiation.

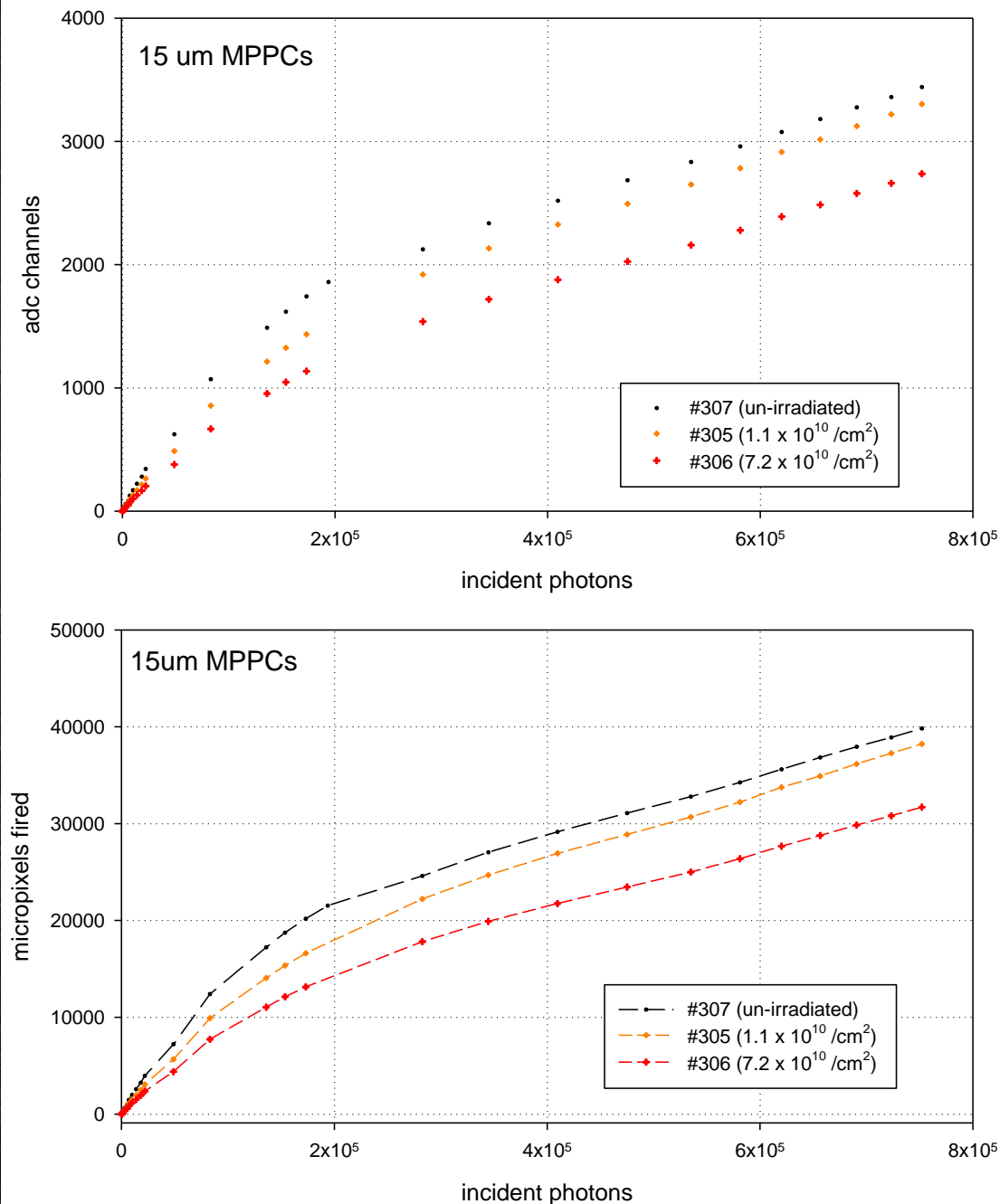
neutron irradiation at LANSCE



Dark current vs bias voltage, measured before and after irradiation.

neutron irradiation at LANSCE

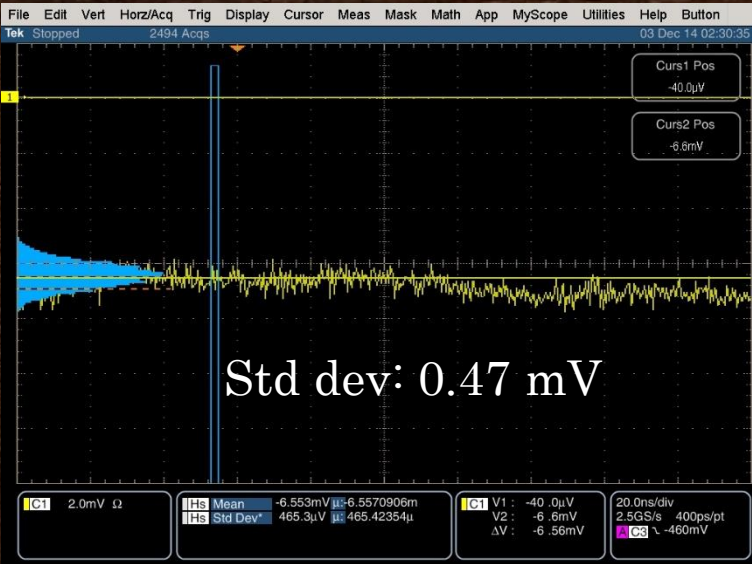
Note (added 8/17): As discussed at the mtg, these measurements were taken at constant V_{supply} without compensating for decreased gain from the increased current and change in the actual voltage drop across the sipm.



MPPCs - sPHENIX preamp /LED pulser peak and pedestal measured after irradiation ($7.2 \times 10^{10} / \text{cm}^2$).

pedestal

Before irradiation

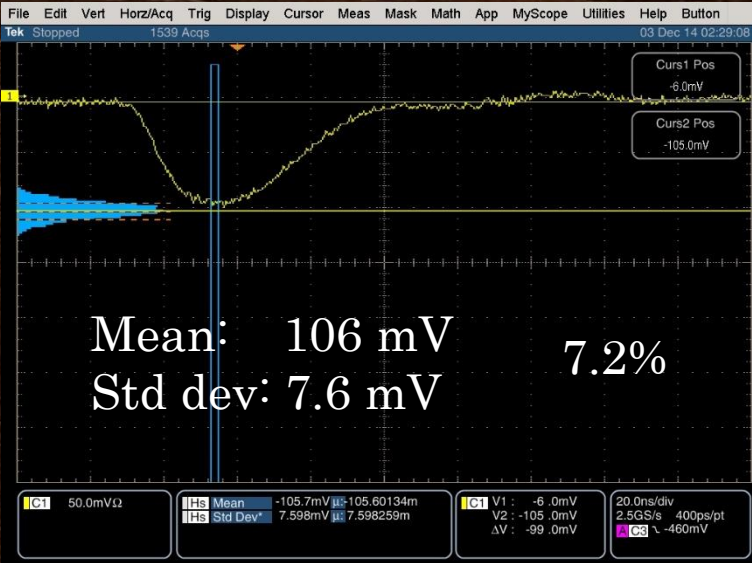


After irradiation

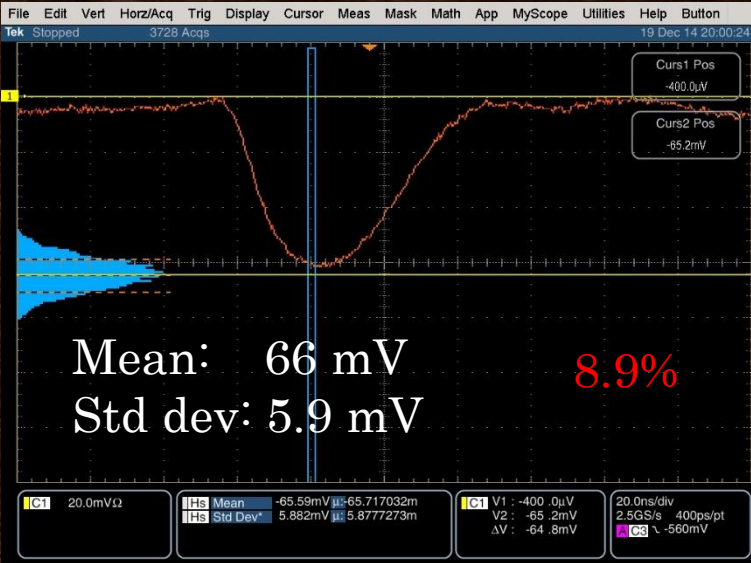


Peak

Mean: 106 mV
Std dev: 7.6 mV
7.2%



Mean: 66 mV
Std dev: 5.9 mV
8.9%



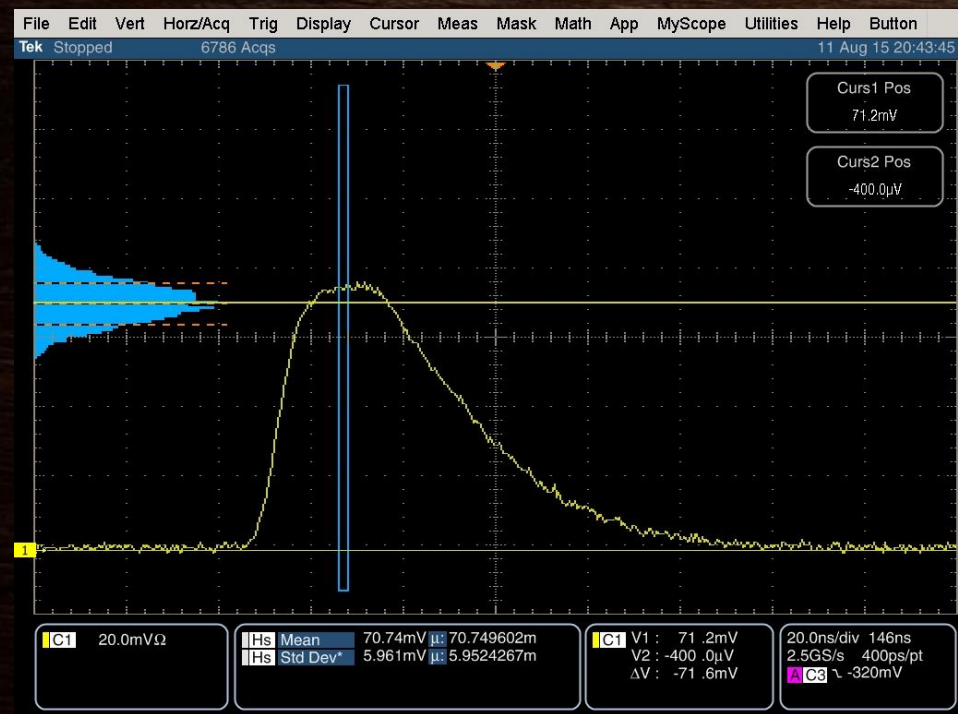
neutron irradiation
at LANSCE

Combined Test of -015P sipm and sPhenix preamp

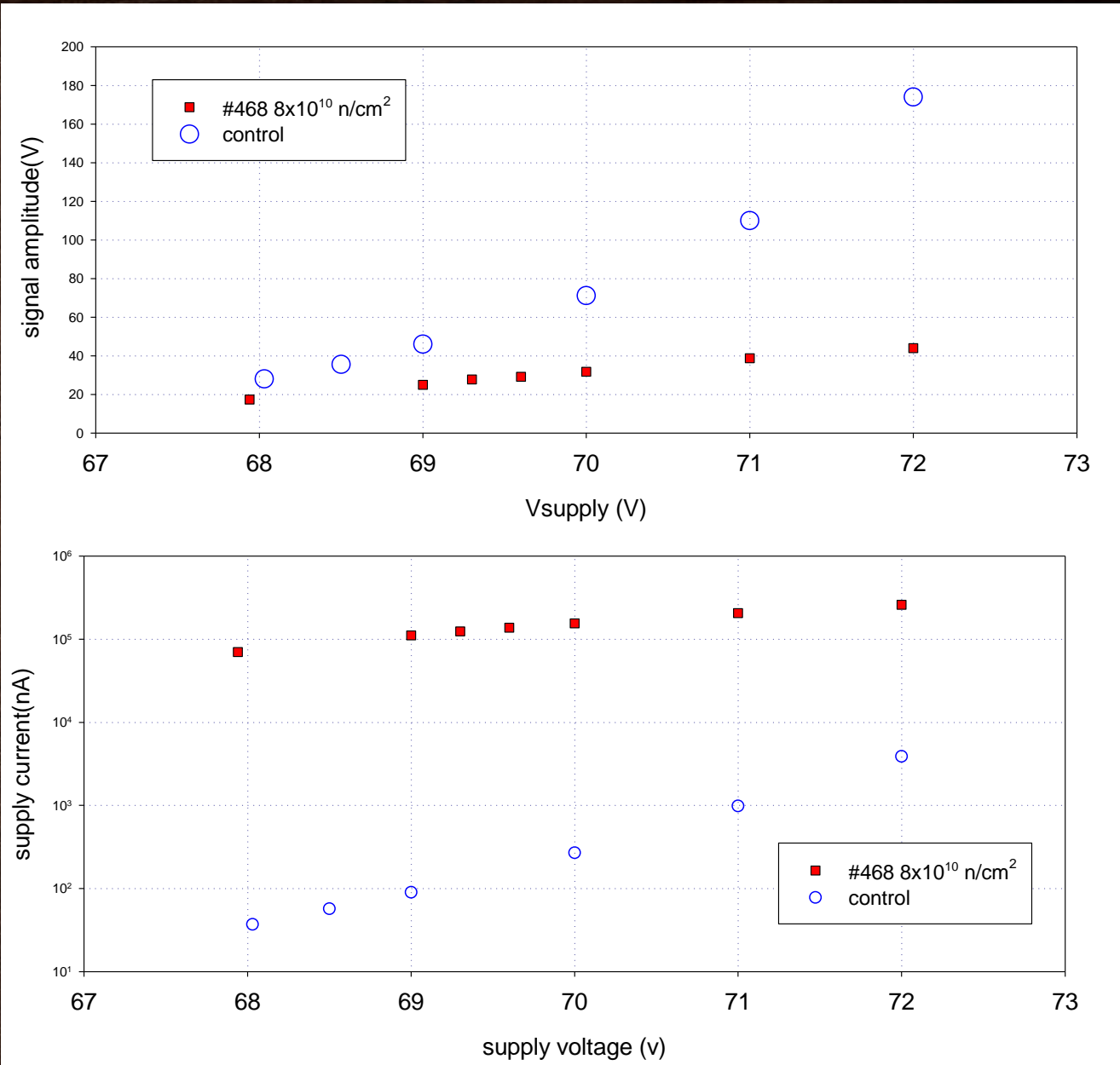
LED - pulsed sipm

observable effects of radiation exposure:

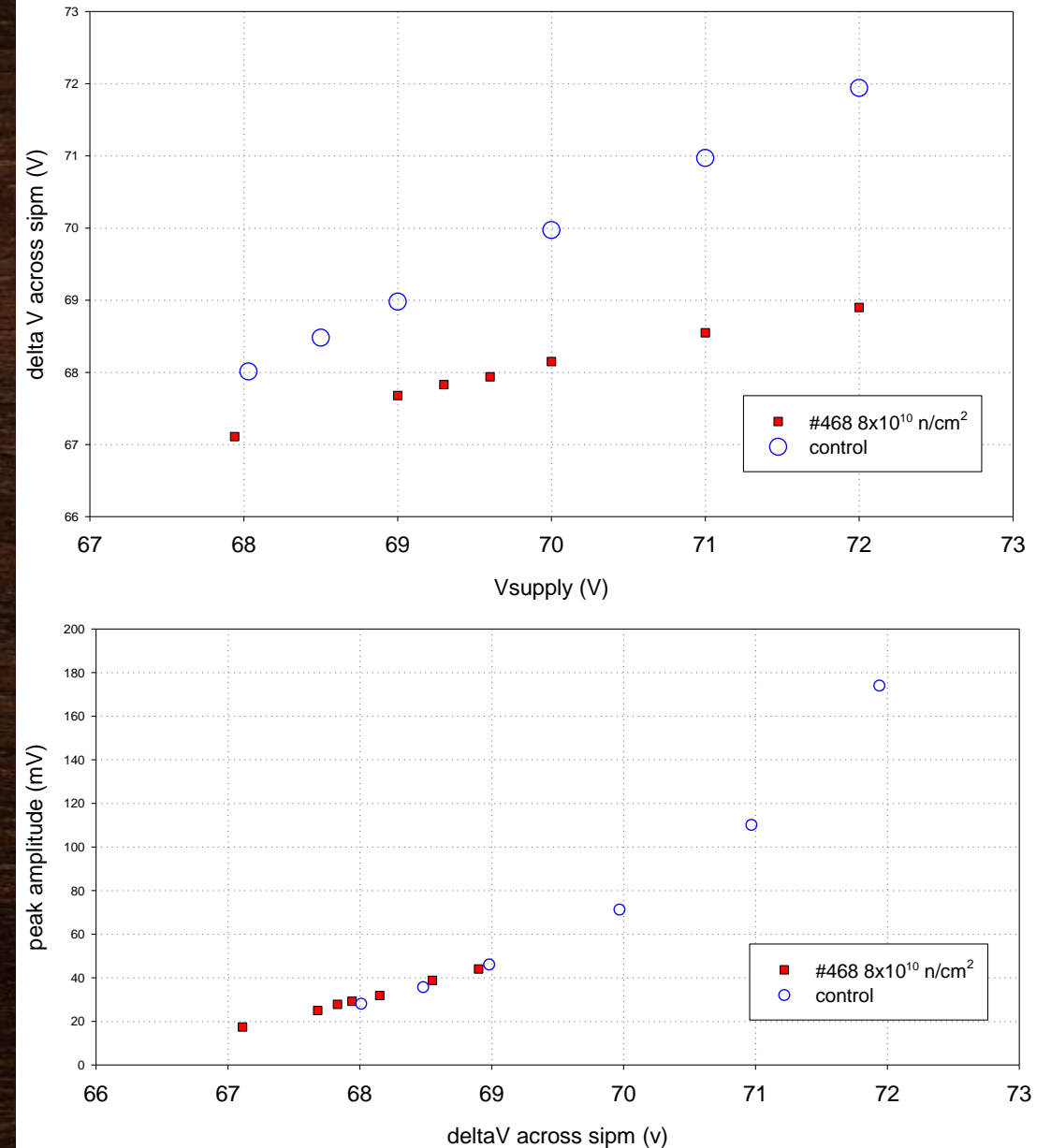
- signal amplitude decreases
- supply current increase



Sipm/Preamp output pulse



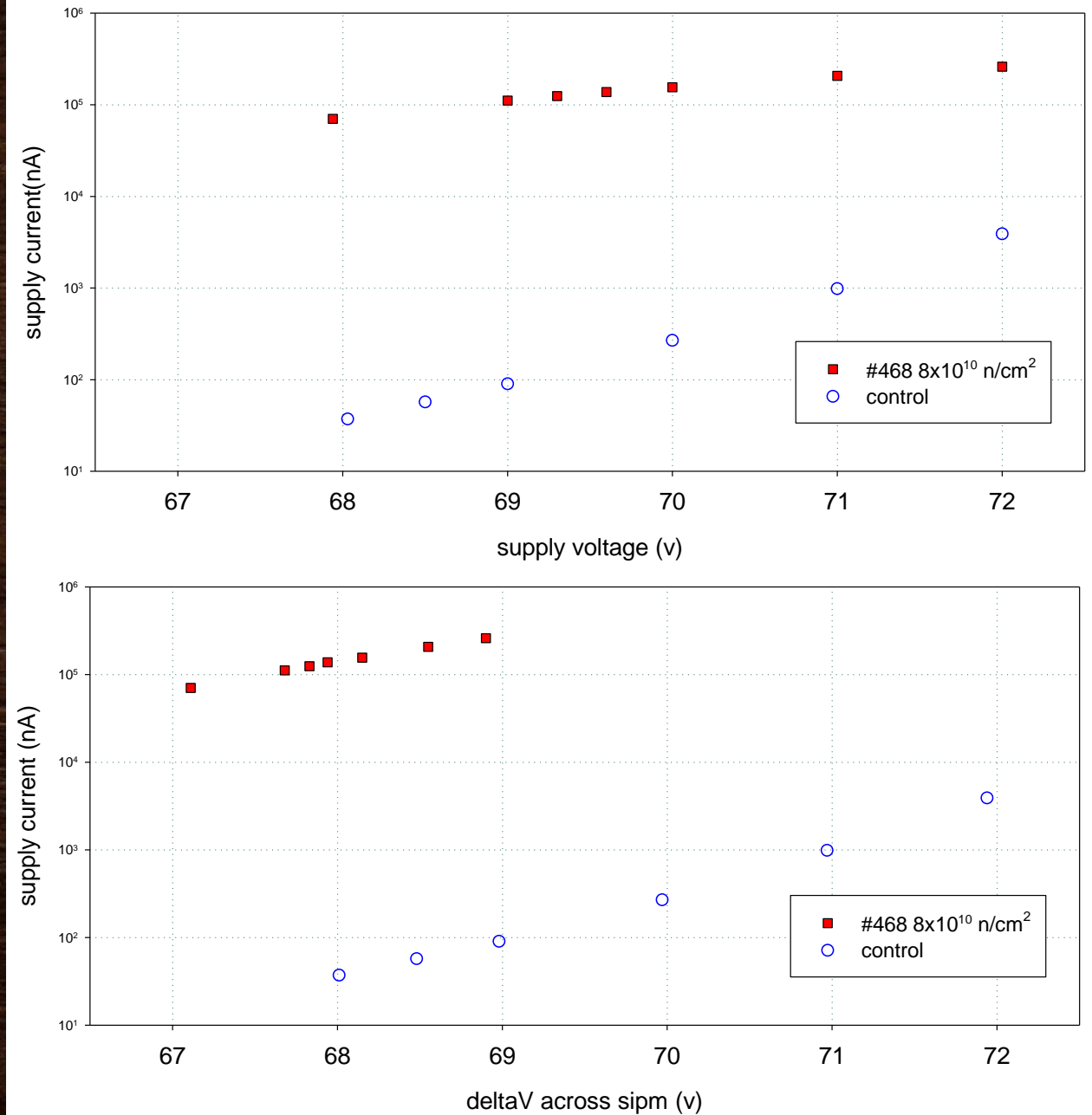
- In the undamaged (control) sipm, ΔV across the sipm $\sim V_{\text{supply}}$
- In the damaged device, $\Delta V < V_{\text{supply}}$
- After irradiation, we observe a decrease in signal amplitude at constant supply voltage.
- Radiation Damage causes an increase in the sipm dark current. The increase in dark current results in greater voltage drop across resistive elements in the circuit, which causes a drop in the voltage across the sipm thereby reducing the sipm gain.
- If we maintain the actual ΔV across the sipm and plot peak amplitude vs ΔV , there is little if any change in the signal amplitude before and after irradiation to $8 \times 10^{10} \text{ n/cm}^2$.



Change in sipm dark current after irradiation.

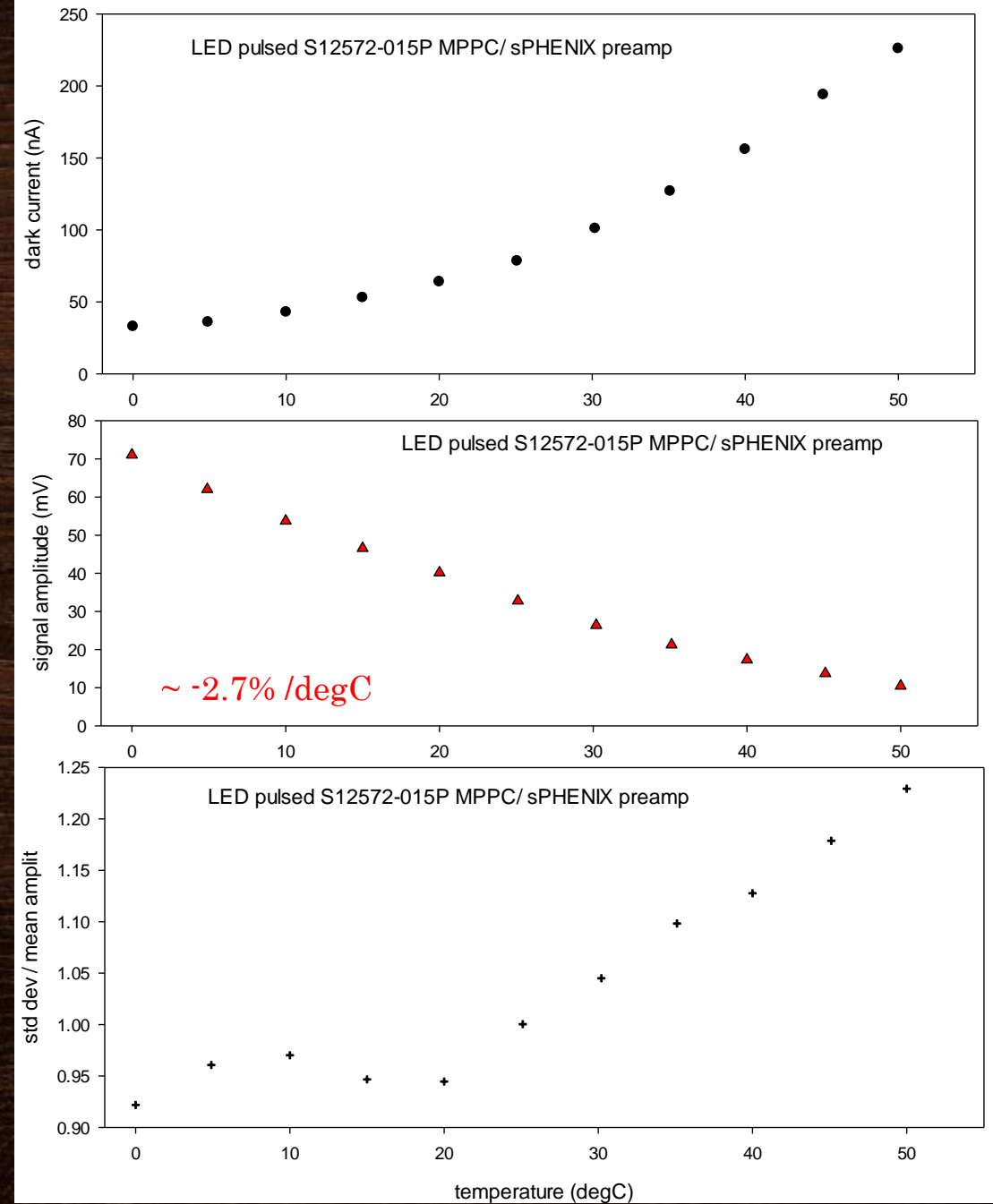
Change in current after correction for voltage drop.

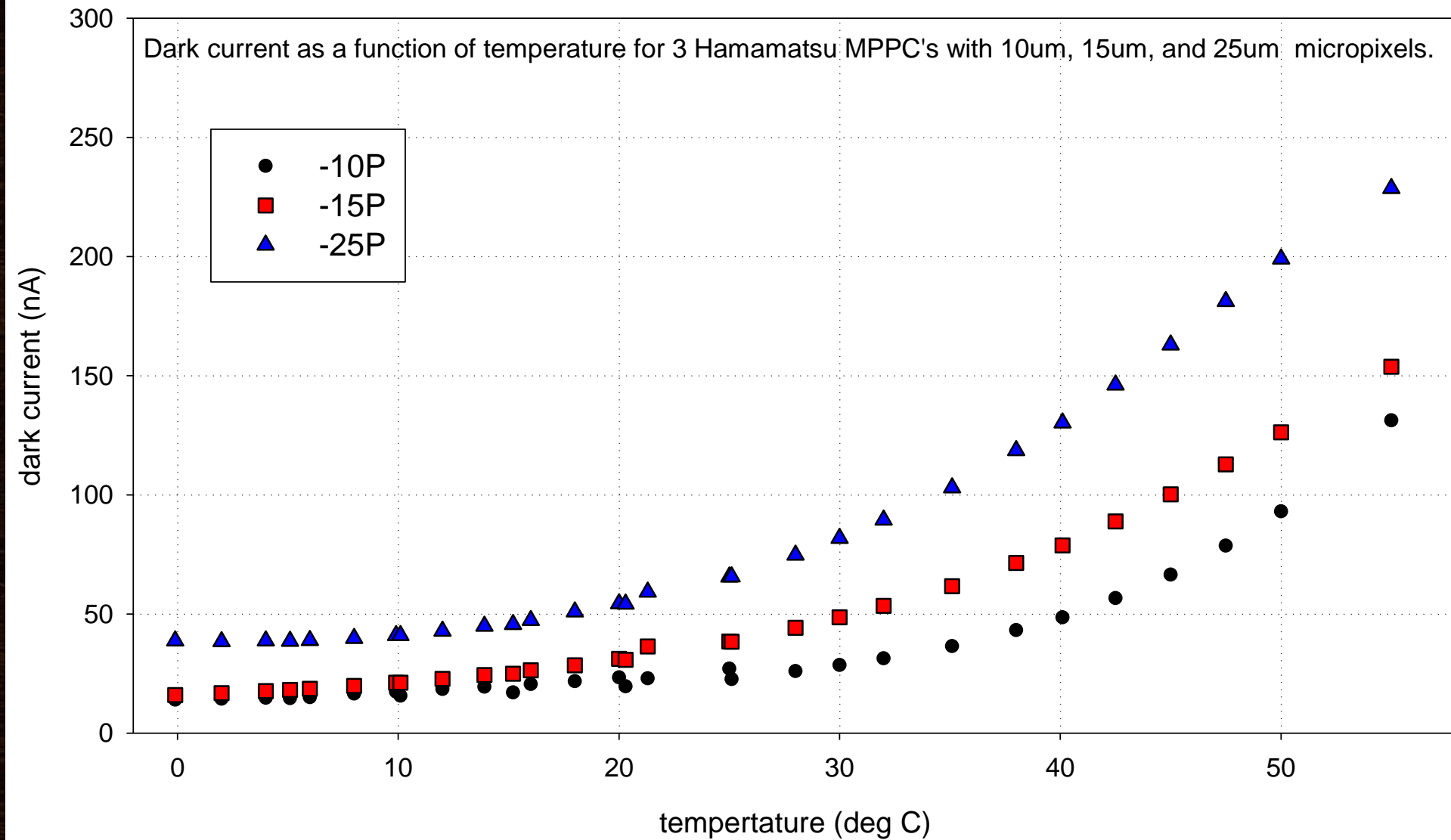
Increasing V_{supply} to keep the delta V across the sipm (and the gain) constant, results in an additional increase in the sipm circuit current.



EFFECT OF TEMPERATURE ON COMBINED MPPC+PREAMP

- S12572-015P MPPC / sPhenix preamp
 - pulsed LED
 - MPPC and Preamp inside temperature controlled cell
 - dark current increases with temperature
 - signal amplitude (gain) decreases with temperature
 - noise increases with temperature





Sipm dark current vs temp. (no preamp)